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ON Semiconductor®

# FGB3040G2-F085 / FGD3040G2-F085 FGP3040G2-F085 / FGI3040G2-F085

## EcoSPARK<sup>®</sup> 2 300mJ, 400V, N-Channel Ignition IGBT

### Features

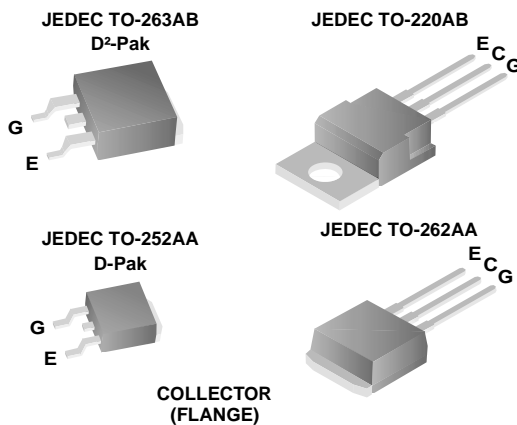
- SCIS Energy = 300mJ at  $T_J = 25^\circ\text{C}$
- Logic Level Gate Drive
- Qualified to AEC Q101
- RoHS Compliant



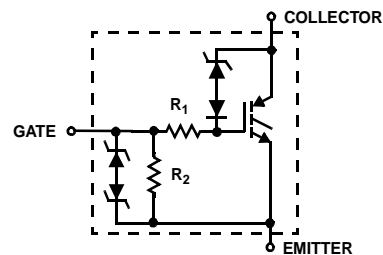
### Applications

- Automotive Ignition Coil Driver Circuits
- Coil On Plug Applications

### Package



### Symbol



### Device Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
$BV_{CER}$	Collector to Emitter Breakdown Voltage ( $I_C = 1\text{mA}$ )	400	V
$BV_{ECS}$	Emitter to Collector Voltage - Reverse Battery Condition ( $I_C = 10\text{mA}$ )	28	V
$E_{SCIS25}$	Self Clamping Inductive Switching Energy (Note 1)	300	mJ
$E_{SCIS150}$	Self Clamping Inductive Switching Energy (Note 2)	170	mJ
$I_{C25}$	Collector Current Continuous, at $V_{GE} = 5.0\text{V}$ , $T_C = 25^\circ\text{C}$	41	A
$I_{C110}$	Collector Current Continuous, at $V_{GE} = 5.0\text{V}$ , $T_C = 110^\circ\text{C}$	25.6	A
$V_{GEM}$	Gate to Emitter Voltage Continuous	$\pm 10$	V
$P_D$	Power Dissipation Total, at $T_C = 25^\circ\text{C}$	150	W
	Power Dissipation Derating, for $T_C > 25^\circ\text{C}$	1	W/ $^\circ\text{C}$
$T_J$	Operating Junction Temperature Range	-55 to +175	$^\circ\text{C}$
$T_{STG}$	Storage Junction Temperature Range	-55 to +175	$^\circ\text{C}$
$T_L$	Max. Lead Temp. for Soldering (Leads at 1.6mm from case for 10s)	300	$^\circ\text{C}$
$T_{PKG}$	Reflow soldering according to JESD020C	260	$^\circ\text{C}$
ESD	HBM-Electrostatic Discharge Voltage at 100pF, 1500 $\Omega$	4	kV
	CDM-Electrostatic Discharge Voltage at 1 $\Omega$	2	kV

## Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FGB3040G2	FGB3040G2-F085	TO-263AB	330mm	24mm	800
FGD3040G2	FGD3040G2-F085	TO-252AA	330mm	16mm	2500
FGP3040G2	FGP3040G2-F085	TO-220AB	Tube	N/A	50
FGI3040G2	FGI3040G2-F085	TO-262AA	Tube	N/A	50

## Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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### Off State Characteristics

$BV_{\text{CER}}$	Collector to Emitter Breakdown Voltage	$I_{\text{CE}} = 2\text{mA}, V_{\text{GE}} = 0,$ $R_{\text{GE}} = 1\text{K}\Omega,$ $T_J = -40 \text{ to } 150^\circ\text{C}$	370	400	430	V	
$BV_{\text{CES}}$	Collector to Emitter Breakdown Voltage	$I_{\text{CE}} = 10\text{mA}, V_{\text{GE}} = 0\text{V},$ $R_{\text{GE}} = 0,$ $T_J = -40 \text{ to } 150^\circ\text{C}$	390	420	450	V	
$BV_{\text{ECS}}$	Emitter to Collector Breakdown Voltage	$I_{\text{CE}} = -20\text{mA}, V_{\text{GE}} = 0\text{V},$ $T_J = 25^\circ\text{C}$	28	-	-	V	
$BV_{\text{GES}}$	Gate to Emitter Breakdown Voltage	$I_{\text{GES}} = \pm 2\text{mA}$	$\pm 12$	$\pm 14$	-	V	
$I_{\text{CER}}$	Collector to Emitter Leakage Current	$V_{\text{CE}} = 250\text{V}, R_{\text{GE}} = 1\text{K}\Omega$	$T_J = 25^\circ\text{C}$	-	-	25	$\mu\text{A}$
			$T_J = 150^\circ\text{C}$	-	-	1	mA
$I_{\text{ECS}}$	Emitter to Collector Leakage Current	$V_{\text{EC}} = 24\text{V},$	$T_J = 25^\circ\text{C}$	-	-	1	mA
			$T_J = 150^\circ\text{C}$	-	-	40	mA
$R_1$	Series Gate Resistance		-	120	-	$\Omega$	
$R_2$	Gate to Emitter Resistance		10K	-	30K	$\Omega$	

### On State Characteristics

$V_{\text{CE(SAT)}}$	Collector to Emitter Saturation Voltage	$I_{\text{CE}} = 6\text{A}, V_{\text{GE}} = 4\text{V},$	$T_J = 25^\circ\text{C}$	-	1.15	1.25	V
$V_{\text{CE(SAT)}}$	Collector to Emitter Saturation Voltage	$I_{\text{CE}} = 10\text{A}, V_{\text{GE}} = 4.5\text{V},$	$T_J = 150^\circ\text{C}$	-	1.35	1.50	V
$V_{\text{CE(SAT)}}$	Collector to Emitter Saturation Voltage	$I_{\text{CE}} = 15\text{A}, V_{\text{GE}} = 4.5\text{V},$	$T_J = 150^\circ\text{C}$	-	1.68	1.85	V
$E_{\text{SCIS}}$	Self Clamped Inductive Switching	$L = 3.0 \text{ mHy}, R_G = 1\text{K}\Omega,$ $V_{\text{GE}} = 5\text{V}, (\text{Note } 1)$	$T_J = 25^\circ\text{C}$	-	-	300	mJ

### Thermal Characteristics

$R_{\theta\text{JC}}$	Thermal Resistance Junction to Case		-	-	1	$^\circ\text{C/W}$
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### Notes:

1: Self Clamping Inductive Switching Energy ( $E_{\text{SCIS}25}$ ) of 300 mJ is based on the test conditions that starting  $T_J = 25^\circ\text{C}$ ;  $L = 3\text{mHy}$ ,  $I_{\text{SCIS}} = 14.2\text{A}$ ,  $V_{\text{CC}} = 100\text{V}$  during inductor charging and  $V_{\text{CC}} = 0\text{V}$  during the time in clamp.

2: Self Clamping Inductive Switching Energy ( $E_{\text{SCIS}150}$ ) of 170 mJ is based on the test conditions that starting  $T_J = 150^\circ\text{C}$ ;  $L = 3\text{mHy}$ ,  $I_{\text{SCIS}} = 10.8\text{A}$ ,  $V_{\text{CC}} = 100\text{V}$  during inductor charging and  $V_{\text{CC}} = 0\text{V}$  during the time in clamp.

**Electrical Characteristics**  $T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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**Dynamic Characteristics**

$Q_{G(ON)}$	Gate Charge	$I_{CE} = 10\text{A}, V_{CE} = 12\text{V}, V_{GE} = 5\text{V}$	-	21	-	nC		
$V_{GE(TH)}$	Gate to Emitter Threshold Voltage	$I_{CE} = 1\text{mA}, V_{CE} = V_{GE},$	$T_J = 25^\circ\text{C}$		1.3	1.7	2.2	V
			$T_J = 150^\circ\text{C}$		0.75	1.2	1.8	
$V_{GEP}$	Gate to Emitter Plateau Voltage	$V_{CE} = 12\text{V}, I_{CE} = 10\text{A}$	-	2.8	-	V		

**Switching Characteristics**

$t_{d(ON)R}$	Current Turn-On Delay Time-Resistive	$V_{CE} = 14\text{V}, R_L = 1\Omega$	-	0.9	4	$\mu\text{s}$
$t_{rR}$	Current Rise Time-Resistive	$V_{GE} = 5\text{V}, R_G = 1\text{K}\Omega$ $T_J = 25^\circ\text{C},$	-	1.9	7	$\mu\text{s}$
$t_{d(OFF)L}$	Current Turn-Off Delay Time-Inductive	$V_{CE} = 300\text{V}, L = 1\text{mH},$	-	4.8	15	$\mu\text{s}$
$t_{fL}$	Current Fall Time-Inductive	$V_{GE} = 5\text{V}, R_G = 1\text{K}\Omega$ $I_{CE} = 6.5\text{A}, T_J = 25^\circ\text{C},$	-	2.0	15	$\mu\text{s}$

## Typical Performance Curves

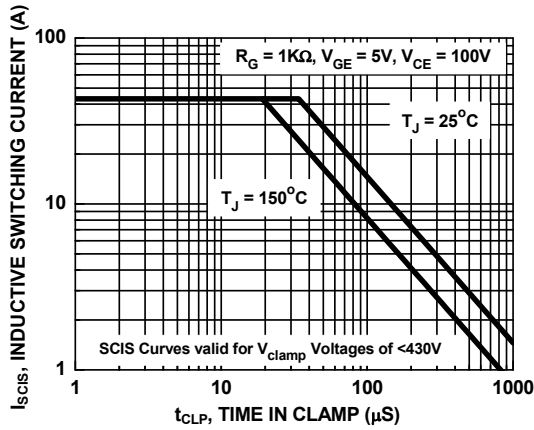


Figure 1. Self Clamped Inductive Switching Current vs. Time in Clamp

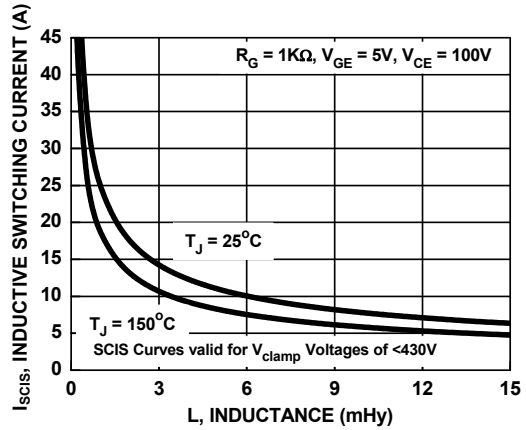


Figure 2. Self Clamped Inductive Switching Current vs. Inductance

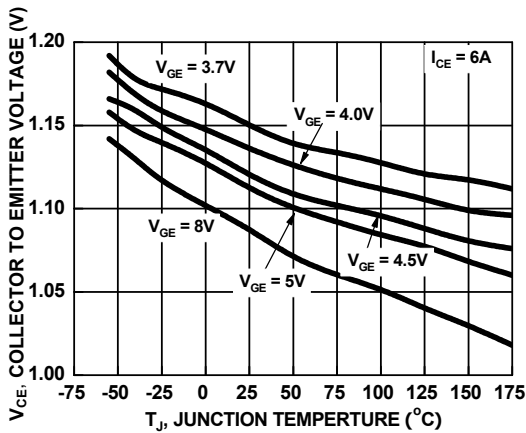


Figure 3. Collector to Emitter On-State Voltage vs. Junction Temperature

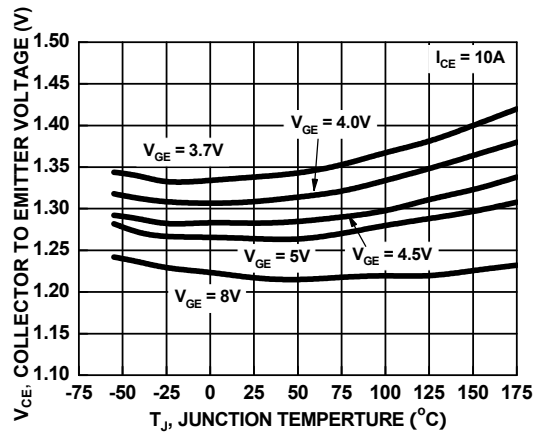


Figure 4. Collector to Emitter On-State Voltage vs. Junction Temperature

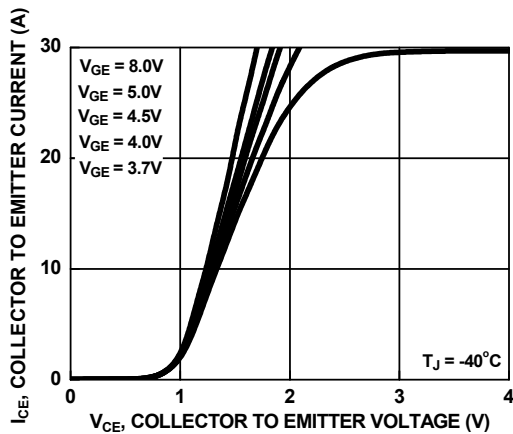


Figure 5. Collector to Emitter On-State Voltage vs. Collector Current

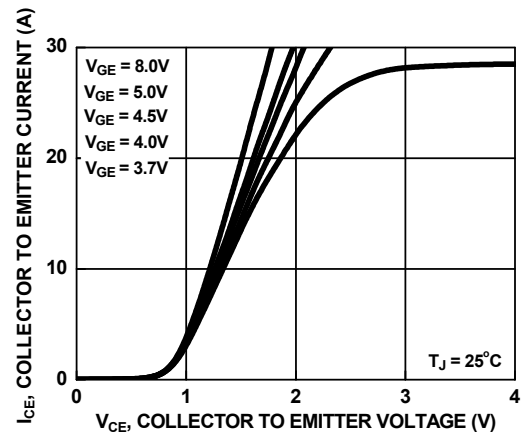
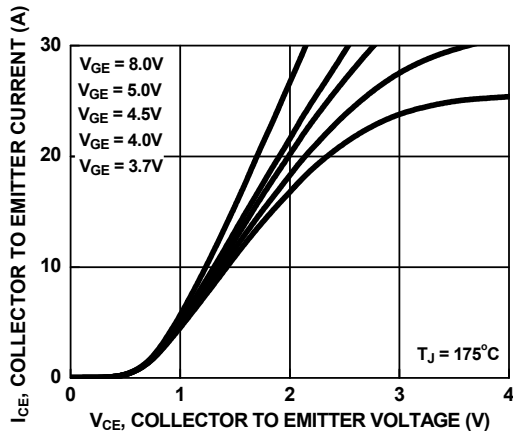
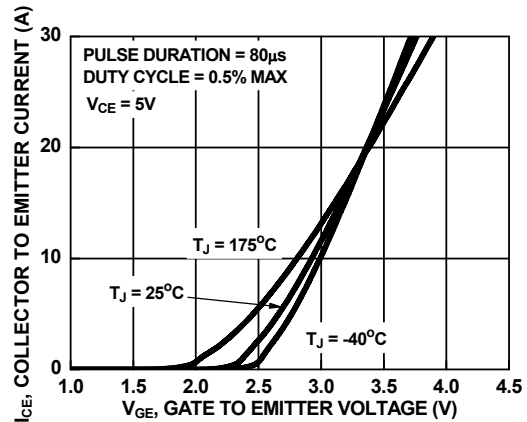


Figure 6. Collector to Emitter On-State Voltage vs. Collector Current

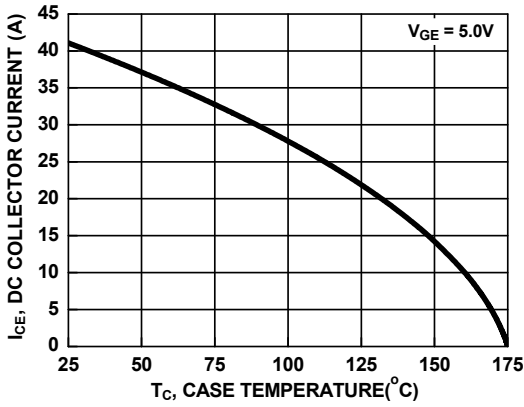
**Typical Performance Curves** (Continued)



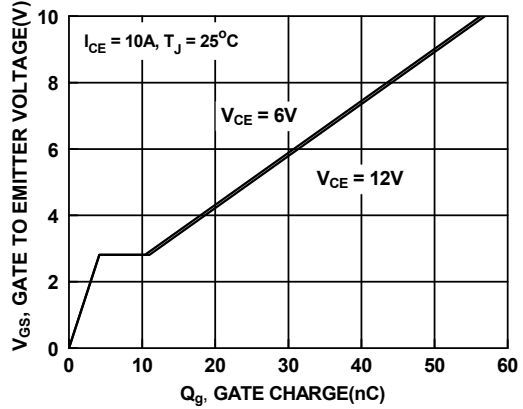
**Figure 7. Collector to Emitter On-State Voltage vs. Collector Current**



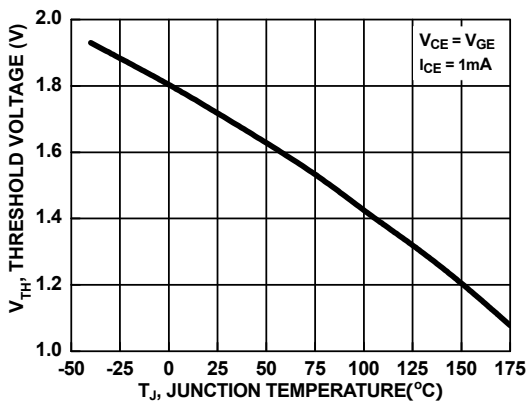
**Figure 8. Transfer Characteristics**



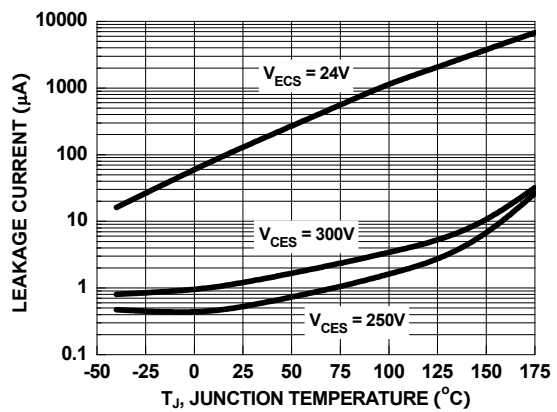
**Figure 9. DC Collector Current vs. Case Temperature**



**Figure 10. Gate Charge**

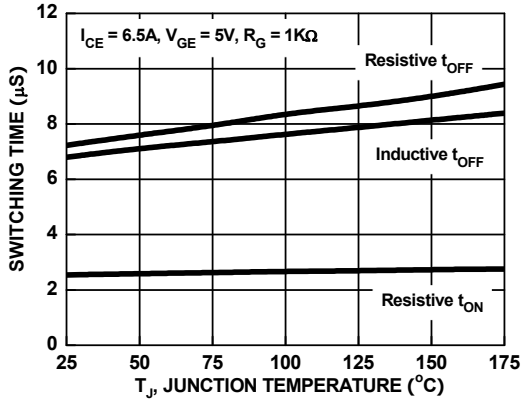


**Figure 11. Threshold Voltage vs. Junction Temperature**

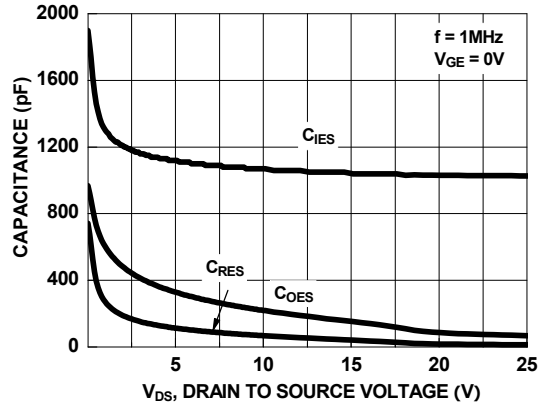


**Figure 12. Leakage Current vs. Junction Temperature**

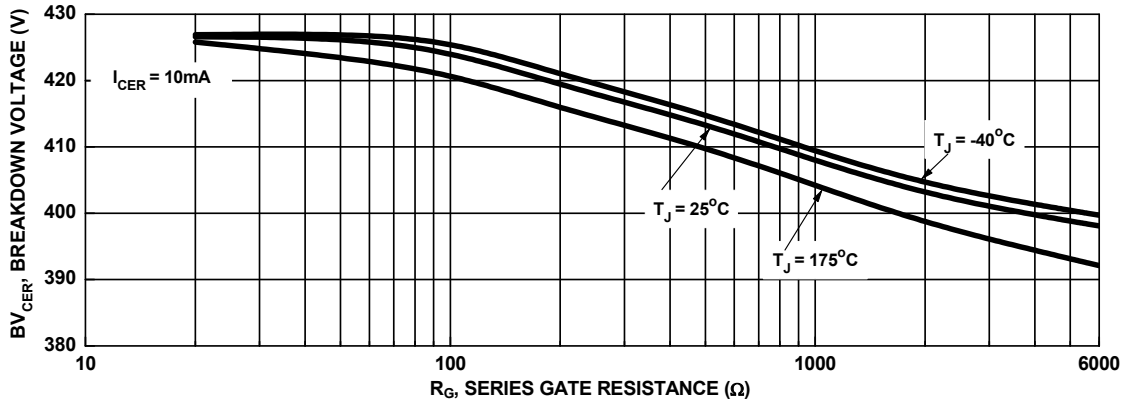
**Typical Performance Curves** (Continued)



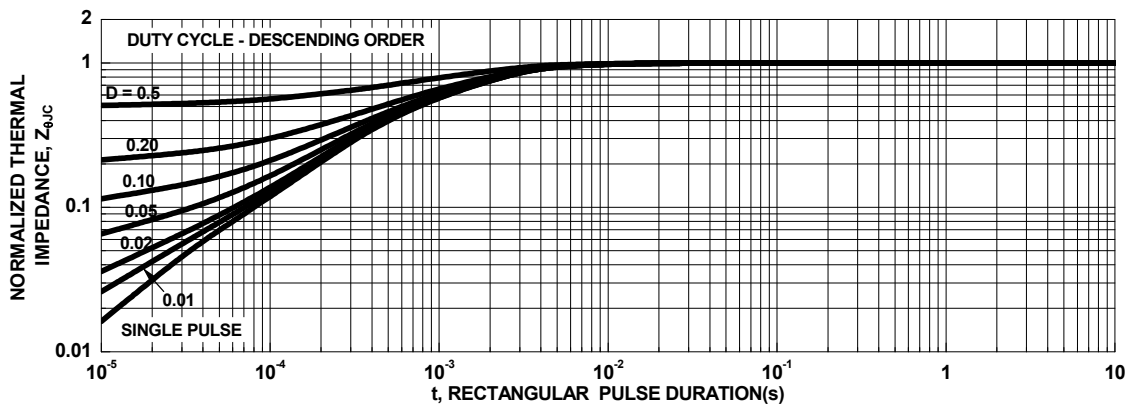
**Figure 13. Switching Time vs. Junction Temperature**



**Figure 14. Capacitance vs. Collector to Emitter Voltage**



**Figure 15. Break down Voltage vs. Series Gate Resistance**



**Figure 16. IGBT Normalized Transient Thermal Impedance, Junction to Case**

### Typical Performance Curves

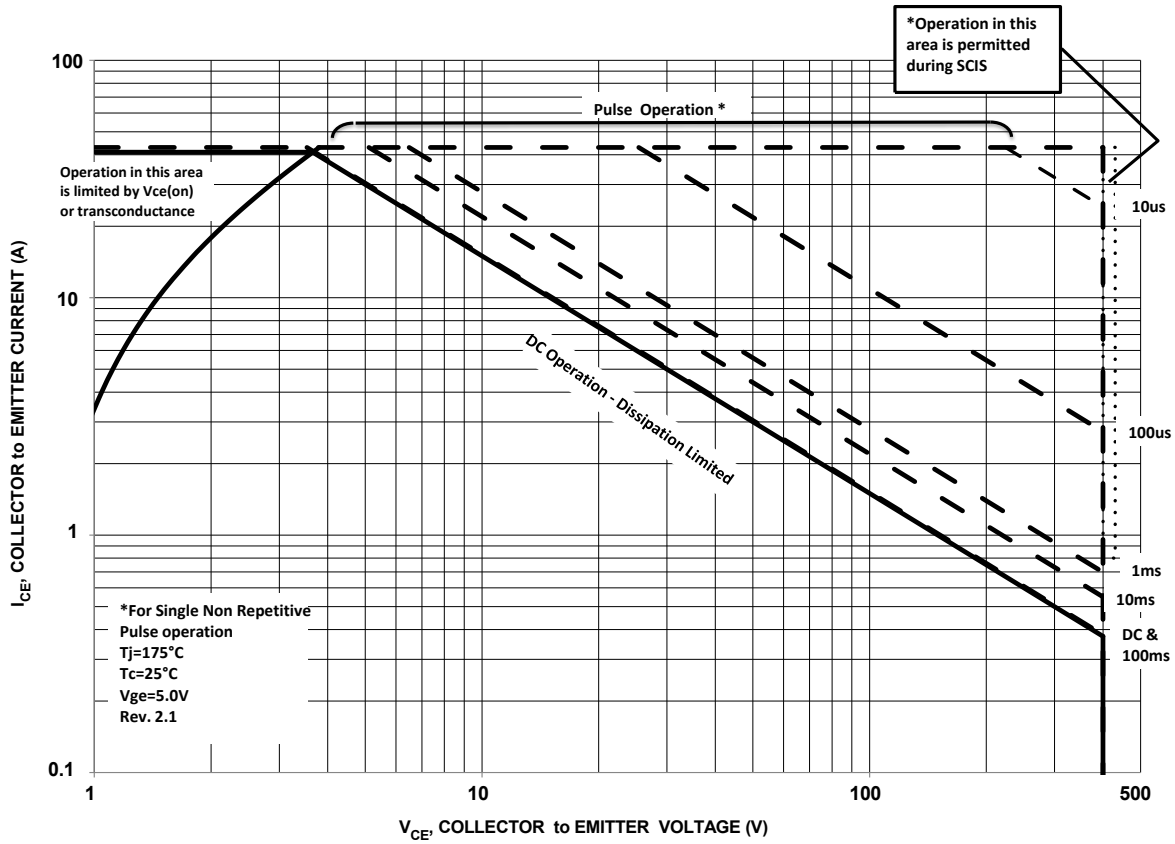


Figure 17. Forward Safe Operating Area



### Test Circuit and Waveforms

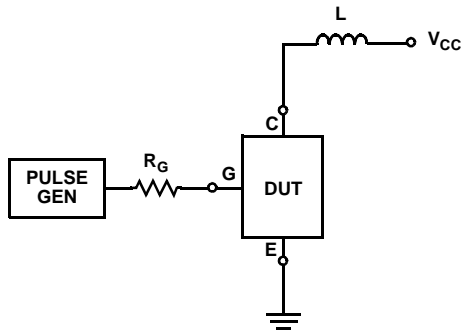


Figure 18. Inductive Switching Test Circuit

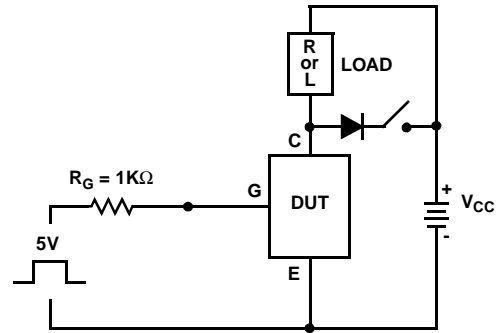


Figure 19.  $t_{ON}$  and  $t_{OFF}$  Switching Test Circuit

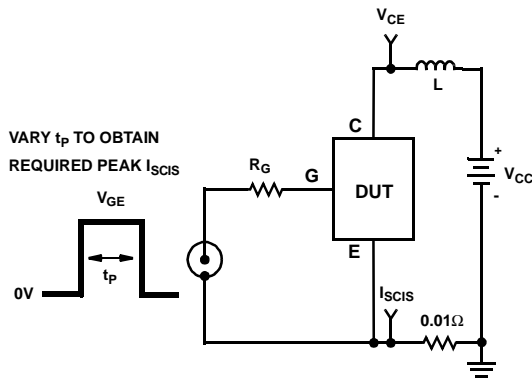


Figure 20. Energy Test Circuit

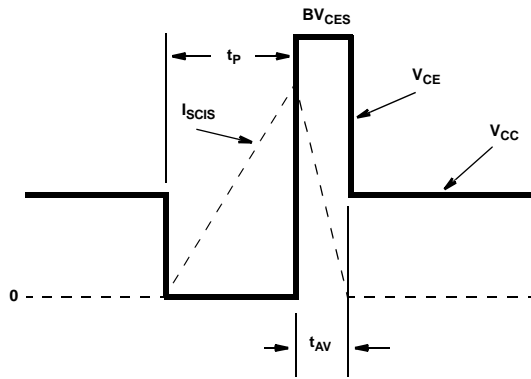



Figure 21. Energy Waveforms

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